

## Complementary power transistors

#### **Features**

- Low collector-emitter saturation voltage
- Complementary NPN-PNP transistors

#### **Applications**

- General purpose
- Audio amplifier

#### **Description**

The devices are manufactured in planar technology with "base island" layout. The resulting transistors show exceptional high gain performance coupled with very low saturation voltage.

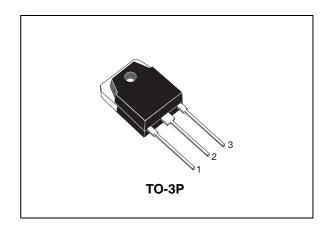


Figure 1. Internal schematic diagrams

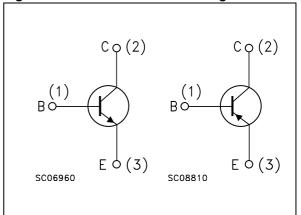


Table 1. Device summary

Order code	Marking	Package	Packaging
TIP35CP	TIP35CP	TO-3P	Tube
TIP36CP	TIP36CP	10-36	Tube

September 2008 Rev 2 1/9

Electrical ratings TIP35CP - TIP36CP

# 1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter		Value	Unit
		NPN	TIP35CP	
		PNP	TIP36CP	
V <sub>CBO</sub>	Collector-base voltage (I <sub>E</sub> = 0)		100	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)		100	V
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)		5	V
I <sub>C</sub>	Collector current		25	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)		50	Α
I <sub>B</sub>	Base current		5	Α
P <sub>tot</sub>	Total dissipation at T <sub>case</sub> = 25 °C		125	W
T <sub>stg</sub>	Storage temperature		-65 to 150	°C
T <sub>J</sub>	Max. operating junction temperature		150	°C

For PNP type voltage and current values are negative.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max	1	°C/W

## 2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C; \text{ unless otherwise specified})$ 

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CEO</sub>	Collector cut-off current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 60 V			1	mA
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			1	mA
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 100 V			0.7	mA
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 30 mA	100			٧
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_C = 15 \text{ A}$ $I_B = 1.5 \text{ A}$ $I_C = 25 \text{ A}$ $I_B = 5 \text{ A}$			1.8 4	V V
V <sub>BE(on)</sub> <sup>(1)</sup>	Base-emitter voltage	$I_C = 15 \text{ A}$ $V_{CE} = 4 \text{ V}$ $I_C = 25 \text{ A}$ $V_{CE} = 4 \text{ V}$			2 4	V V
h <sub>FE</sub> <sup>(1)</sup>	DC current gain	$I_C = 1.5 \text{ A}$ $V_{CE} = 4 \text{ V}$ $I_C = 15 \text{ A}$ $V_{CE} = 4 \text{ V}$	25 10		50	
f <sub>T</sub>	Transition frequency	$I_C = 1 \text{ A}$ $V_{CE} = 10 \text{ V}$ $f = 1 \text{ MHz}$	3			MHz

<sup>1.</sup> Pulsed duration = 300 ms, duty cycle  $\geq$  1.5%.

For PNP type voltage and current are negative.

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Electrical characteristics TIP35CP - TIP36CP

#### 2.1 Electrical characteristic (curves)

Figure 2. DC current gain for NPN type Figure 3. DC current gain for PNP type

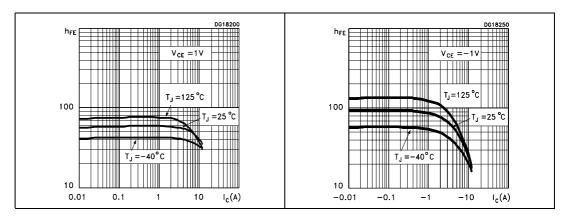


Figure 4. DC current gain for NPN type Figure 5. DC current gain for PNP type

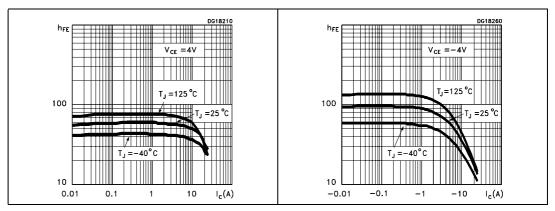


Figure 6. Collector-emitter saturation Figure 7. Collector-emitter saturation voltage for NPN type Voltage for PNP type

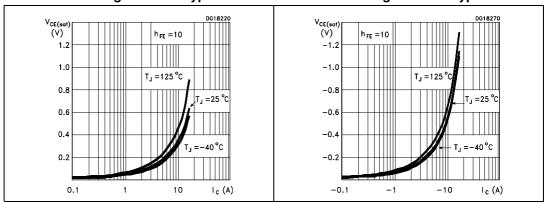


Figure 8. Base-emitter saturation voltage for NPN type

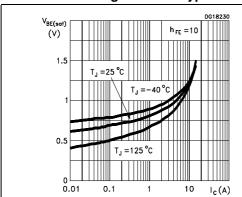


Figure 9. Base-emitter saturation voltage for PNP type

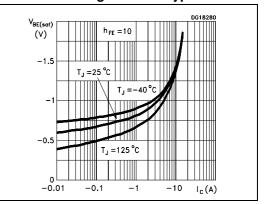
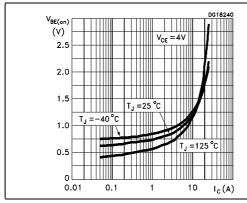
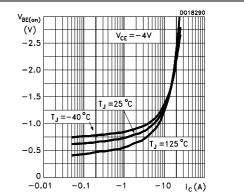


Figure 10. Base-emitter on voltage for NPN type

Figure 11. Base-emitter on voltage for PNP type





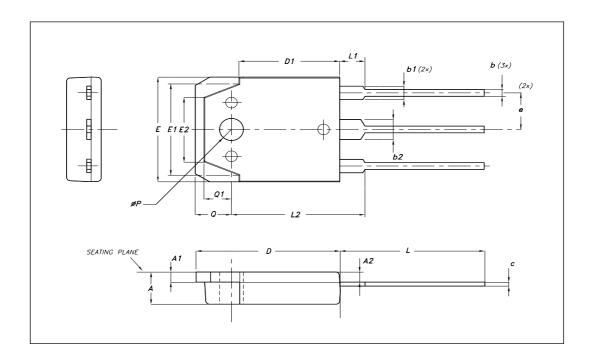
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## 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: <a href="https://www.st.com">www.st.com</a>

#### **TO-3P Mechanical data**

DIM.		mm.	
	MIN.	TYP	MAX.
Α	4.6		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
С	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
е	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
Р	3.10		3.30
Q		5	
Q1		3.80	



Revision history TIP35CP - TIP36CP

# 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
21-Apr-2008	1	Initial release
23-Sep-2008	2	Added figures 2, 3, 4, 5, 6, 7, 8, 9, 10, 11.

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